Amendments to the Specification:

Page 8, the paragraph at lines 5-14

Additionally, in the processing apparatus according to the present invention, the first source gas may be selected from a group consisting of $TiCl_4$, TiF_4, $TiBr_4$, TiI_4, $Ti[N(C_2H_5CH_3)]_4$, $Ti[N(CH_3)_2]_4$, $Ti[N(C_2H_5)_2]_4$, TaF_5, $TaCl_5$, $TaBr_5$, TaI_5, $Ta(NC(CH_3)_3)(N(C_2H_5)_2)_3$, ~~$Ta(N(CH_3)_2)(NC_5H_{11})$~~ $Ta(N(CH_3)_2)_3(NC_5H_{11})$, $Ta[N(C_2H_5)_2]_5$, $Ta[N(CH_3)_2]_5$ and $Ta(N(C_2H_5)_2)_3(N(C_2H_5)_2)$, and the second source gas may be selected from a group consisting of NH_3, N_2H_4, $NH(CH_3)_2$ and $N_2H_3(CH_3)$, so as to deposit a TiN film or a TaN film on the processing substrate.

The paragraph bridging pages 25 and 26:

Although the TiN film is produced by $TiCl_4$ and NH_3 in the above-mentioned embodiment, the following film deposition processes, as other examples, can be efficiently performed using the processing apparatus according to the present invention: deposition of a TiN film by TiF_4 and NH_3; deposition of a TiN film by $TiBr_4$ and NH_3; deposition of a TiN film by TiI_4 and NH_3; deposition of a TiN film by $Ti [N(C_2H_5CH_3)]_4$ and NH_3; deposition of a TiN film by $Ti [N(CH_3)_2]_4$ and NH_3; deposition of a TiN film by $Ti[N(C_2H_5)_2]_4$ and NH_3; deposition of a TaN film by TaF_5 and NH_3; deposition of a TaN film by $TaCl_5$ and NH_3; deposition of a TaN film by $TaBr_5$ and NH_3; deposition of a TaN film by TaI_5 and NH_3; deposition of a TaN film by $Ta(NC(CH_3)_3)(N(C_2H5)_2)_3$ and NH_3;

deposition of a TaN film by ~~$Ta(N(CH_3)_2)(NC_5H_{11})$~~ $\underline{Ta(N(CH_3)_2)_3(NC_5H_{11})}$ and NH_3; deposition of a TaN film by $Ta[N(C_2H_5)_2]_5$ and NH_3; deposition of a TaN film by $Ta[N(CH_3)_2]_5$ and NH_3; deposition of a TaN film by $Ta(N(C_2H_5)_2)_3(N(C_2H_5)_2)$ and NH_3; deposition of a WN film by WF_6 and NH_3; deposition of a Al_2O_3 film by $Al(CH_3)_3$ and H_2O; deposition of a Al_2O_3 film by $Al(CH_3)_3$ and H_2O_2; deposition of a ZrO_2 film by $Zr(O\text{-}t(C_4H_4))_4$ and H_2O; deposition of a ZrO_2 film by $Zr(O\text{-}t(C_4H_4))_4$ and H_2O_2; deposition of a Ta_2O_5 film by $Ta(OC_2H_5)_5$ and H_2O; deposition of a Ta_2O_5 film by $Ta(OC_2H_5)_5$ and H_2O_2; and deposition of a Ta_2O_5 film by $Ta(OC_2H_5)_5$ and O_2.